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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G-; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	0.3	-	5	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 9}}{}$	0.3	-	5	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G+; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	0.3	-	7	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 11</u>	-	-	10	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 1.4 A; T <sub>j</sub> = 25 °C; <u>Fig. 12</u>	-	1.3	1.6	V
Dynamic cha	racteristics					
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 402 V; $T_j$ = 110 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit; Fig. 14	100	-	-	V/µs
dV <sub>com</sub> /dt	rate of change of commutating voltage	$V_D$ = 400 V; $T_j$ = 110 °C; $dI_{com}/$ dt = 0.44 A/ms; gate open circuit	1	-	-	V/µs

# 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	4	T2
2	T2	main terminal 2		G sym051
3	G	gate		Symost
4	T2	main terminal 2	⊟1 ⊟2 ⊟3 SC-73 (SOT223)	

## 6. Ordering information

**Table 3. Ordering information** 

Type number	Package				
	Name	Description	Version		
Z0107MN0	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223		

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# 7. Limiting values

### **Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	600	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_{sp} \le 105 \text{ °C}$ ; $Fig. 1$ ; $Fig. 2$ ; $Fig. 3$	-	1	Α
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 20 ms; Fig. 4; Fig. 5	-	12.5	Α
		full sine wave; T <sub>j(init)</sub> = 25 °C; t <sub>p</sub> = 16.7 ms	-	13.8	Α
l <sup>2</sup> t	I <sup>2</sup> t for fusing	t <sub>p</sub> = 10 ms; SIN	-	0.78	A²s
dl <sub>T</sub> /dt	rate of rise of on-state	I <sub>G</sub> = 20 mA; T2+ G+	-	50	A/µs
	current	I <sub>G</sub> = 20 mA; T2+ G-	-	50	A/µs
		I <sub>G</sub> = 20 mA; T2- G-	-	50	A/µs
		I <sub>G</sub> = 20 mA; T2- G+	-	20	A/µs
I <sub>GM</sub>	peak gate current		-	1	Α
P <sub>GM</sub>	peak gate power		-	2	W
P <sub>G(AV)</sub>	average gate power	over any 20 ms period	-	0.1	W
T <sub>stg</sub>	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C

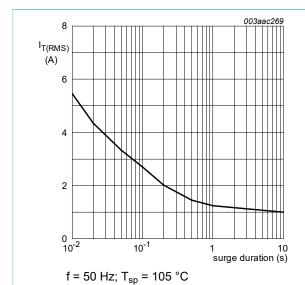


Fig. 1. RMS on-state current as a function of surge duration; maximum values

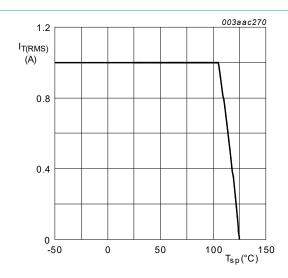


Fig. 2. RMS on-state current as a function of solder point temperature; maximum values

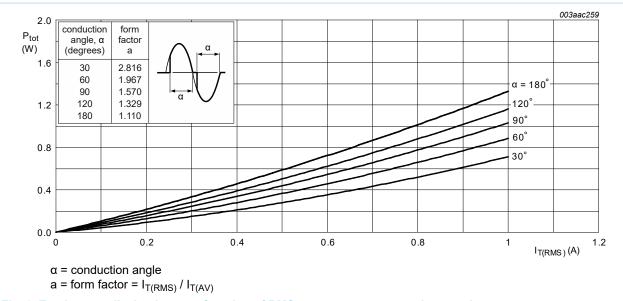


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

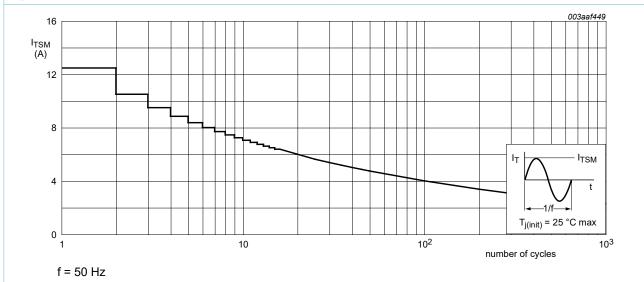
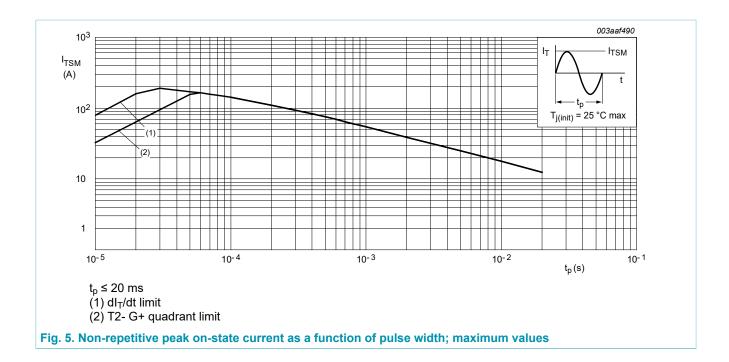


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



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### 8. Thermal characteristics

**Table 5. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point	full cycle; Fig. 6	-	-	15	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient free air	in free air; printed-circuit board mounted: minimum footprint; full cycle; Fig. 7	-	156	-	K/W
		in free air; printed-circuit board mounted: pad area; full cycle; Fig. 8	-	70	-	K/W

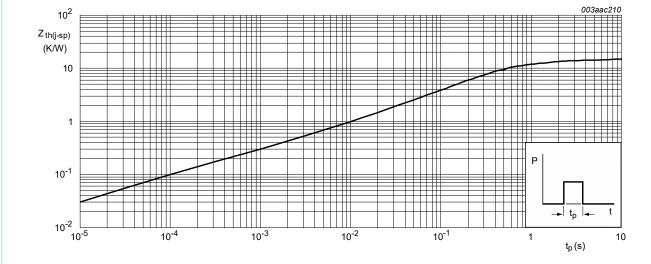
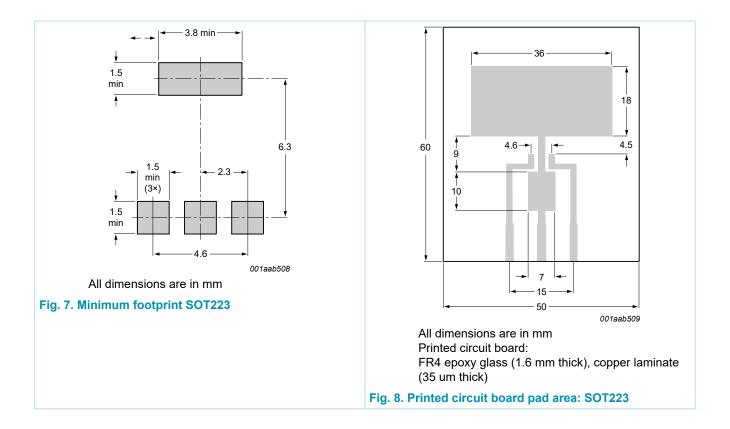


Fig. 6. Transient thermal impedance from junction to solder point as a function of pulse width



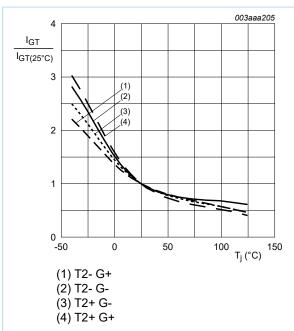
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## 9. Characteristics

### **Table 6. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics		'			
I <sub>GT</sub>	gate trigger current	V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G+; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	0.3	-	5	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 \text{ °C}; Fig. 9$	0.3	-	5	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 9}}{\text{Fig. 9}}$	0.3	-	5	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 9}}$	0.3	-	7	mA
I <sub>L</sub>	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 10$	-	-	10	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; Fig. 10$	-	-	25	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 10}}$	-	-	10	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 10}}$	-	-	10	mA
Н	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 11</u>	-	-	10	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 1.4 A; T <sub>j</sub> = 25 °C; <u>Fig. 12</u>	-	1.3	1.6	V
√ <sub>GT</sub>	gate trigger voltage	$V_D$ = 12 V; $I_T$ = 0.1 A; $T_j$ = 25 °C; Fig. 13	-	-	1	V
		$V_D$ = 600 V; $I_T$ = 0.1 A; $T_j$ = 125 °C; Fig. 13	0.2	-	-	V
D	off-state current	V <sub>D</sub> = 600 V; T <sub>j</sub> = 125 °C	-	-	0.5	mA
Dynamic ch	naracteristics		'			
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 402 V; $T_j$ = 110 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit; Fig. 14	100	-	-	V/µs
dV <sub>com</sub> /dt	rate of change of commutating voltage	$V_D = 400 \text{ V; } T_j = 110 \text{ °C; } dI_{com}/$ dt = 0.44 A/ms; gate open circuit	1	-	-	V/µs

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003aaa203 3 I<sub>L(25°C)</sub> 2 0 -50 0 50 100 150 T<sub>i</sub> (°C)

Fig. 10. Normalized latching current as a function of junction temperature

Fig. 9. Normalized gate trigger current as a function of junction temperature

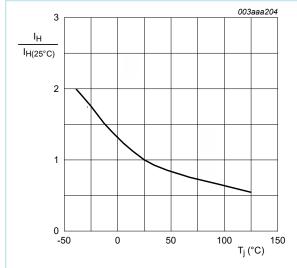
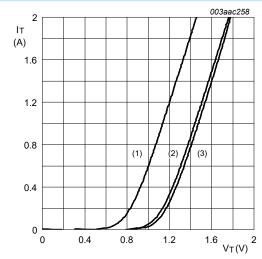


Fig. 11. Normalized holding current as a function of junction temperature



 $V_0 = 1.13 \text{ V}$  $R_s = 0.31 \Omega$ 

(1)  $T_j$  = 125 °C; typical values (2)  $T_j$  = 125 °C; maximum values

(3) T<sub>i</sub> = 25 °C; maximum values

Fig. 12. On-state current as a function of on-state voltage

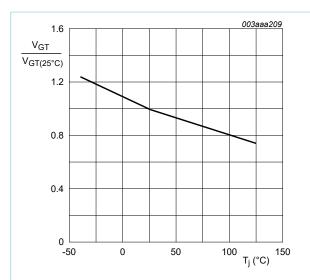


Fig. 13. Normalized gate trigger voltage as a function of junction temperature

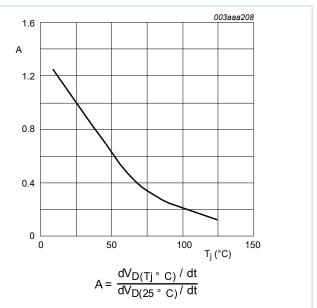
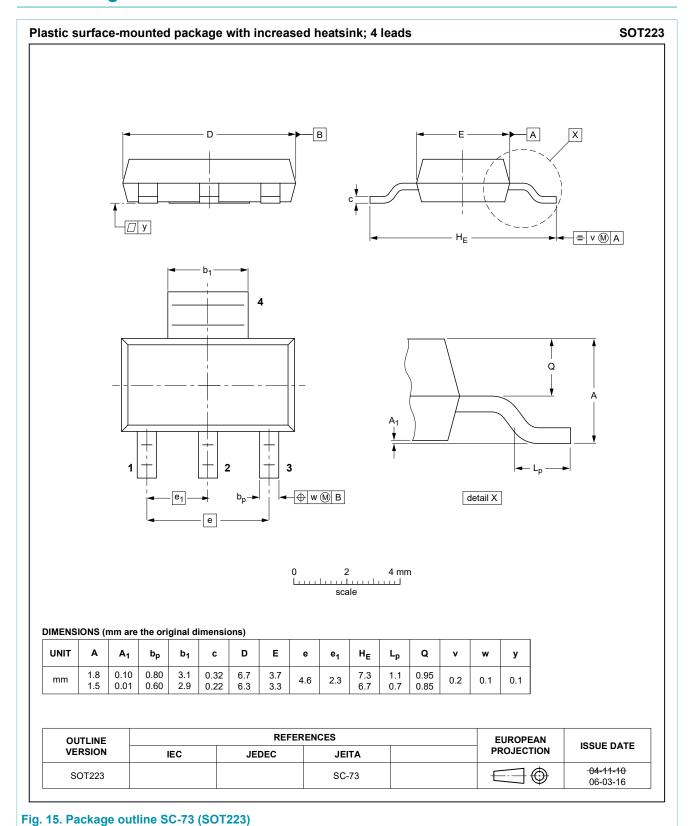


Fig. 14. Normalized critical rate of rise of off-state voltage as a function of junction temperature; typical values

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## 10. Package outline



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## 11. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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